

MITSUBISHI HYBRID IC  
**M57161L-01**

FOR DRIVING TRENCH-GATE IGBT

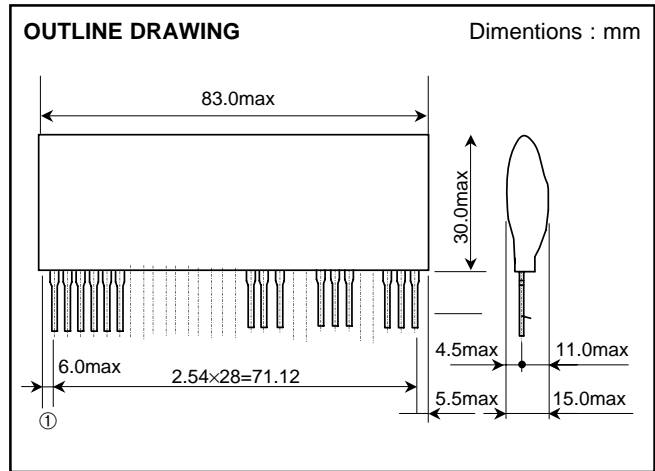
**DESCRIPTION**

M57161L-01 is a hybrid IC designed to drive trench-gate IGBT module with built in RTC.

This device can operate by an input of +15V because of electrical isolation between the input and output by an opto coupler, and the built in DC-DC converter isolated between a pair of positive/negative outputs for gate driving.

With built in protection circuits, this device can maintain a reverse bias for a predetermined time after the detection of an over current (short circuit). Therefore, the protective system operates with a margin of time.

The over current (short circuit) detector functions with RTC circuit built in IGBT module to detect a drop of gate voltage.



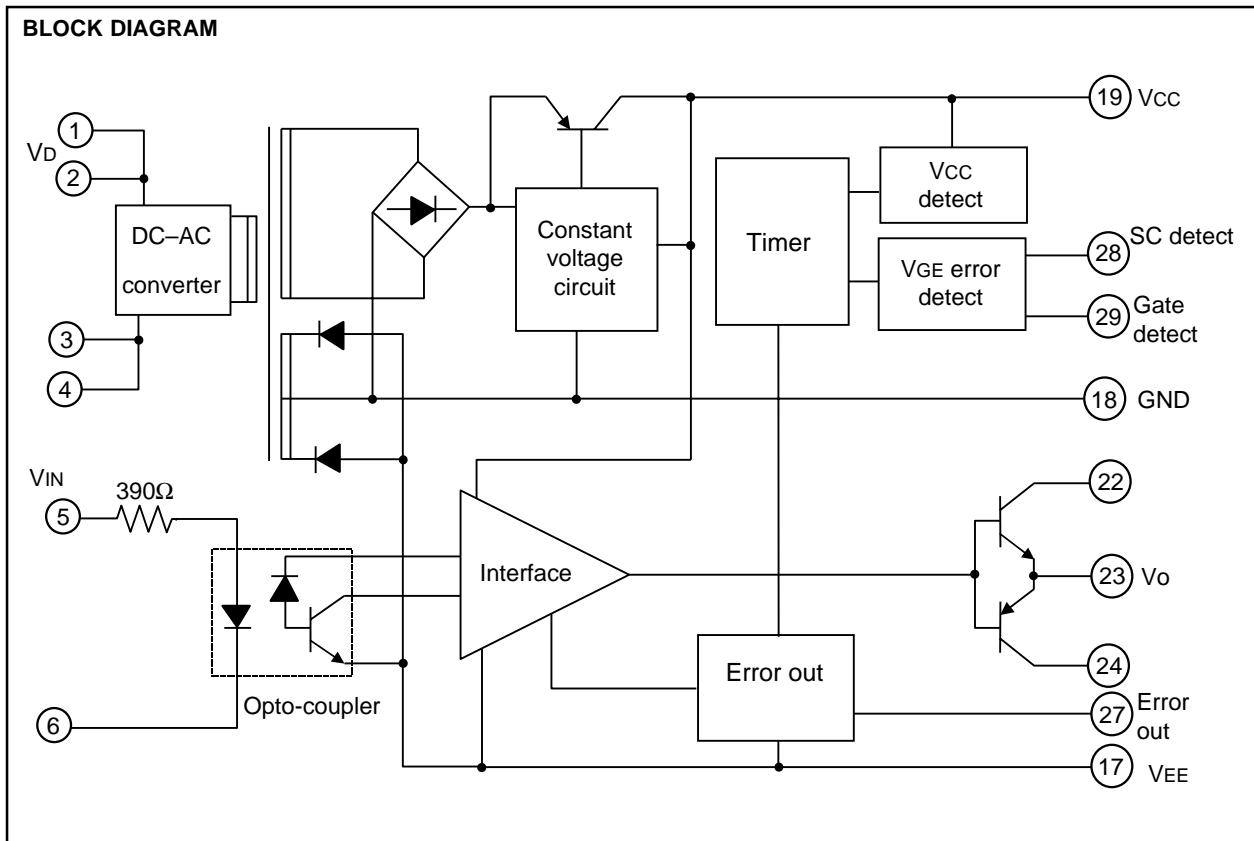
Recommend module ; IGBT module (F)series

**FEATURES**

- Built in insulated DC-DC converter for IGBT drive
- Built in short circuit protection circuit
- Electrical isolation between input and output with opto-coupler ( $V_{ios}=2500V_{rms}$  for 1minute)

**APPLICATION**

To drive IGBT module for inverter or AC servo systems application



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**ABSOLUTE MAXIMUM RATINGS** (Unless otherwise specified, Ta = 25°C)

Symbol	Parameter	Conditions	Ratings	Units
V <sub>D</sub>	Supply voltage		16	V
V <sub>I</sub>	Input voltages	Applied between:⑤-⑥	-1 ~ +7	V
V <sub>O</sub>	Output voltages	At the output voltage "H" V <sub>D</sub> =15.7V	16.5	V
I <sub>OHP</sub>	Output current	Pulse width 1μs, f≤20kHz	-7	A
I <sub>OLP</sub>			7	A
V <sub>iso</sub>	Isolation voltage	Sine-wave voltage 60Hz, 1min	2500	V <sub>rms</sub>
T <sub>c</sub>	Case temperature		85	°C
T <sub>opr</sub>	Operating temperature		-20 ~ +60	°C
T <sub>stg</sub>	Storage temperature		-25 ~ +100	°C
I <sub>FO</sub>	Fault output current	Input current 27pin	25	mA
V <sub>R</sub>	Applied 29 pin		V <sub>CC</sub>	V

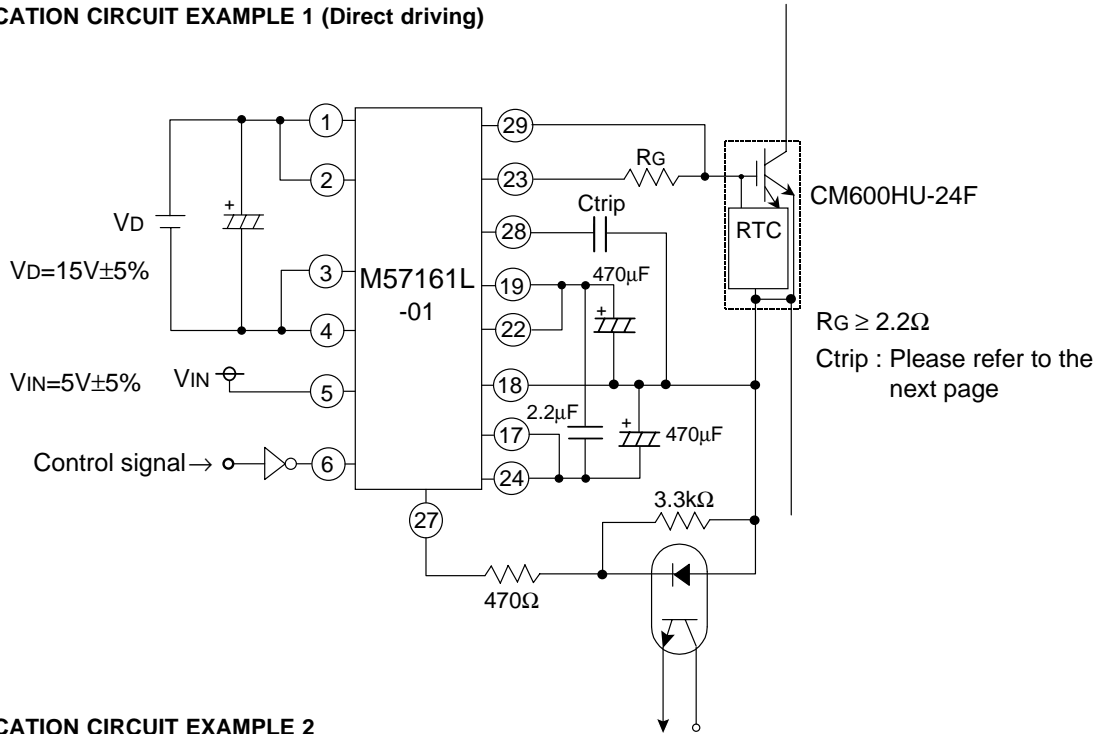
**ELECTRICAL CHARACTERISTICS** (Ta = 25°C, V<sub>D</sub> = 15.0V, V<sub>IN</sub> = 5.0V, f = 20kHz, R<sub>G</sub> = 2.2Ω : CM600HU-24F)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V <sub>D</sub>	Supply voltage	Recommended range	14.3	15.0	15.7	V
V <sub>IN</sub>	Pull-up voltage on input side	Recommended range	4.5	5.0	5.5	V
I <sub>IH</sub>	"H" Input current	Recommended range	9	10	11	mA
f	Switching frequency	Recommended range	—	—	20	kHz
R <sub>G</sub>	Gate resistor	Recommended range	2.2	—	—	Ω
I <sub>IH</sub>	"H" Input current	V <sub>IN</sub> =5V	—	10	—	mA
V <sub>CC</sub>	Gate + supply voltage	V <sub>IN</sub> =0V, f=0Hz	17.0	17.4	17.8	V
V <sub>EE</sub>	Gate - supply voltage	V <sub>IN</sub> =0V, f=0Hz	-5.5	-6.5	-7.5	V
V <sub>OH</sub>	"H" Output voltage		14	15.5	16.5	V
V <sub>OL</sub>	"L" Output voltage		-4.0	-5.0	-6.0	V
t <sub>PLH</sub>	"L-H" Propagation time	I <sub>IH</sub> =10mA	—	0.4	1	μs
t <sub>r</sub>	"L-H" Rise time	I <sub>IH</sub> =10mA	—	0.4	0.5	μs
t <sub>PHL</sub>	"H-L" Propagation time	I <sub>IH</sub> =10mA	—	1.3	2.0	μs
t <sub>f</sub>	"H-L" Fall time	I <sub>IH</sub> =10mA	—	0.4	0.5	μs
t <sub>timer</sub>	Timer	Between start and cancel(Under input signal "L")	1.5	—	2.5	ms
I <sub>FO</sub>	Fault output current	Applied 27pin R=470Ω	—	12	—	mA
t <sub>c</sub>	Controlled time detect delay time	In the rise time 29pin :11V, 28pin :open	—	3.5	—	μs
t <sub>d</sub>	Short-circuit protect delay time	In the rise time 29pin :11V, 28pin :open	—	6.5	—	μs
V <sub>CL</sub>	Start voltage for protection at lower V <sub>CC</sub>	The required minimum of positive power supply for gate when V <sub>O</sub> is in the state of "H"	14.2	15.2	16.2	V
V <sub>SC</sub>	Over-current detect voltage		11.0	11.6	12.2	V

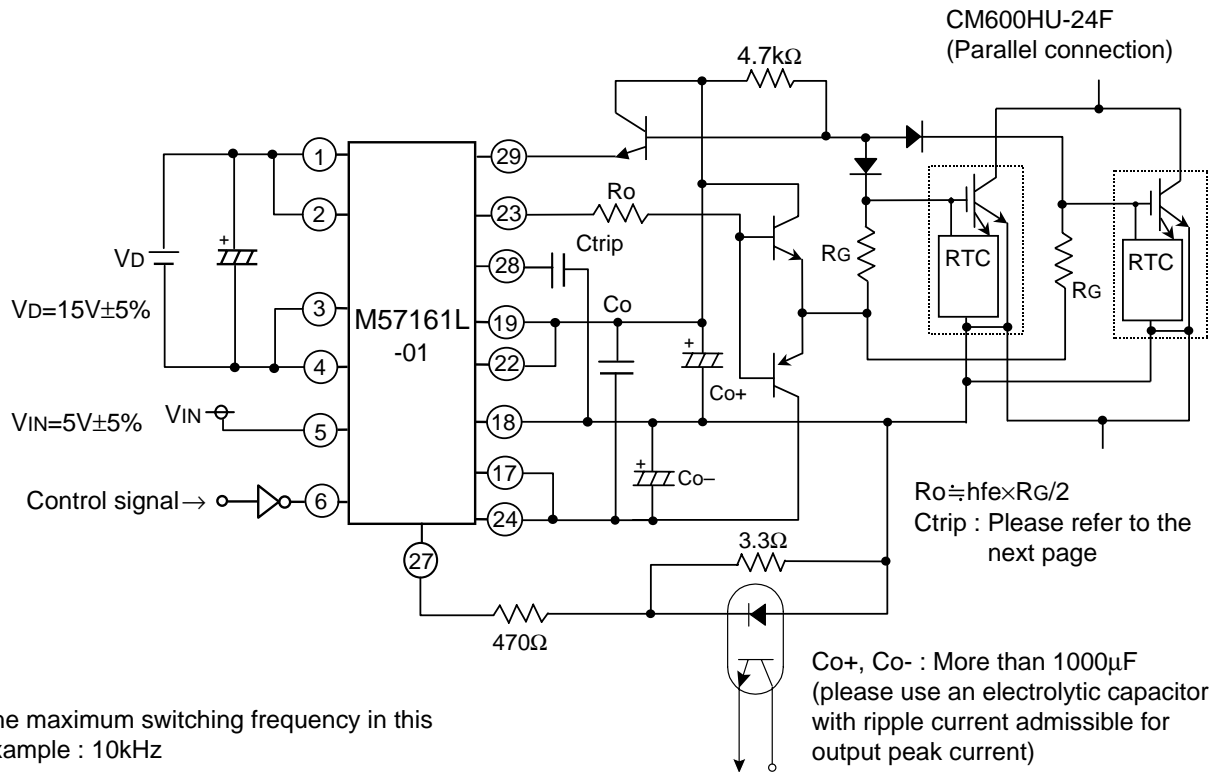
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**APPLICATION CIRCUIT EXAMPLE 1 (Direct driving)**



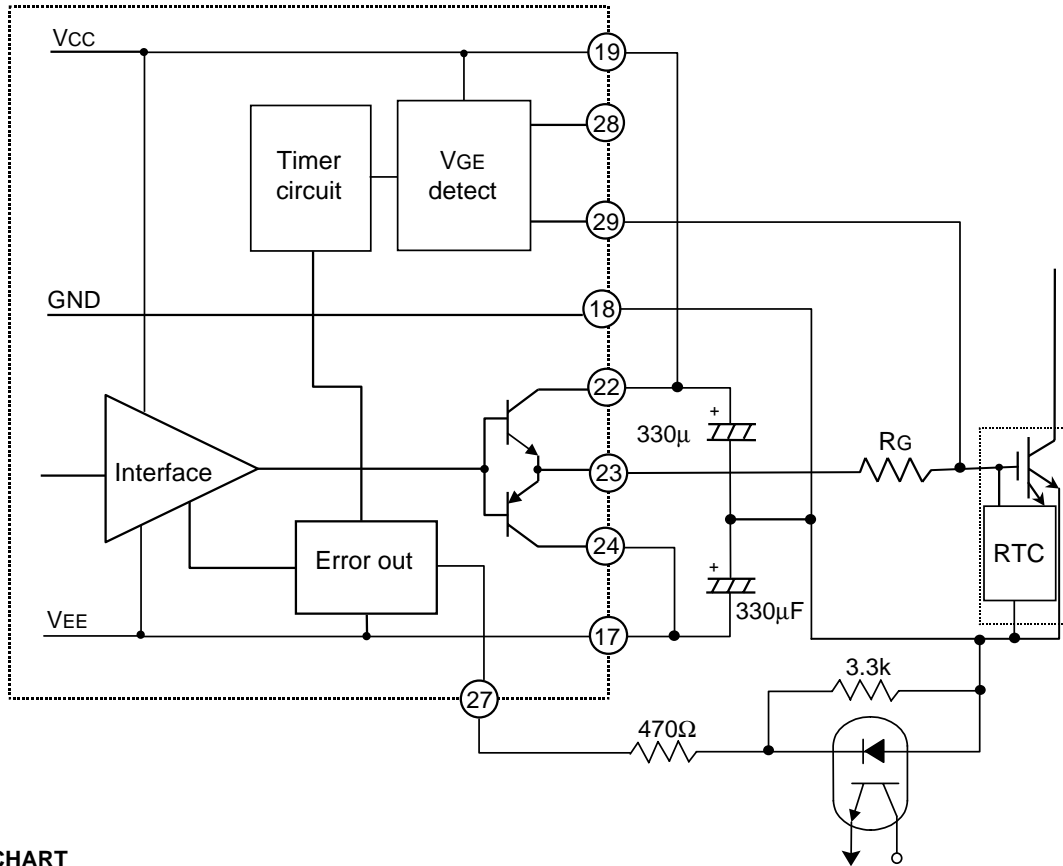
**APPLICATION CIRCUIT EXAMPLE 2 (Additional transistor for output current)**



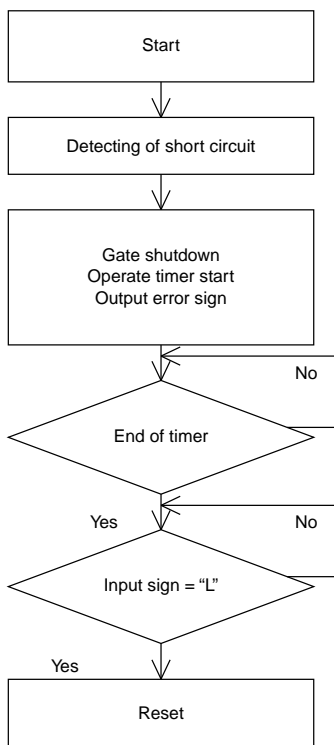
The maximum switching frequency in this example : 10kHz

$C_o$  : A few  $\mu F$   
 The connection to decrease the peak of ripple current

OPERATION OF PROTECTION CIRCUIT



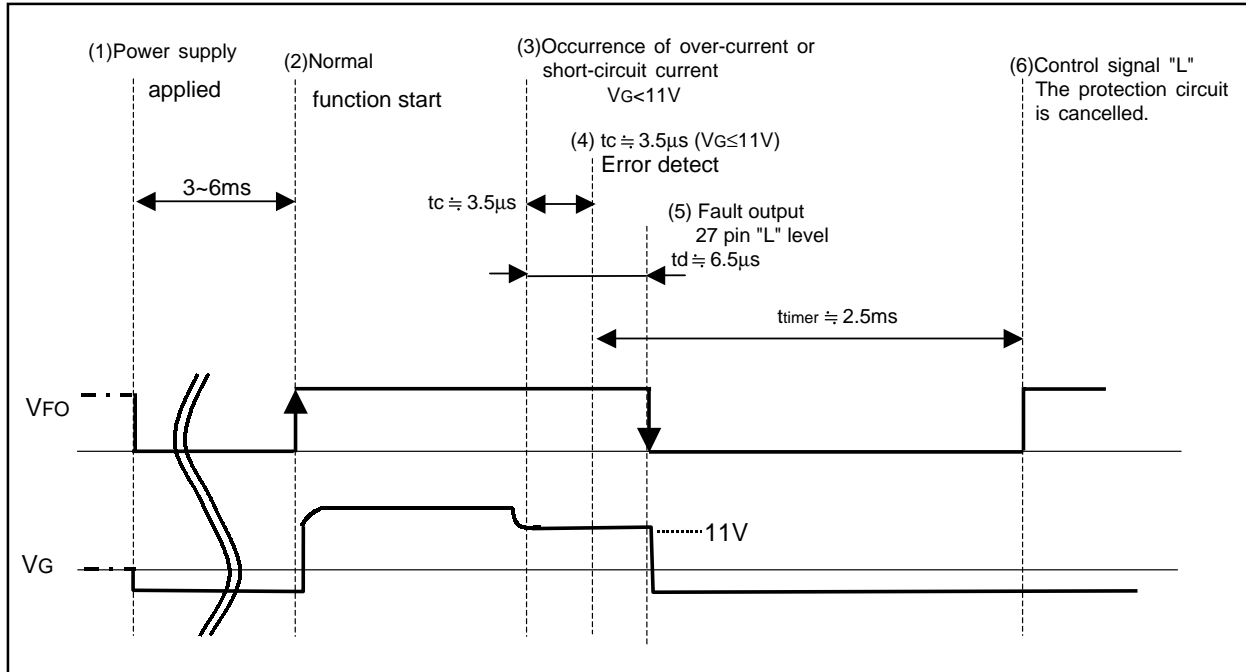
FLOW CHART



1. The V<sub>GE</sub> error detect circuit operates when an input signal is in the state of "H".
2. An error judgment is made when V<sub>GE</sub> becomes below V<sub>sc</sub> (=11v : min).
3. The V<sub>GE</sub> error detect circuit does not function until the time when the gate voltage reaches V<sub>sc</sub> (=12.2V : max).  
The t<sub>c</sub> (=3.5μs) of controlled time detect short circuit is set in order to ensure the turn-on of IGBT modules.
4. If a rise time of gate voltage is longer than 3.5μs, the t<sub>c</sub> can be adjusted by connecting a capacitor (C<sub>trip</sub>) between pins 28 and 18. Please refer to t<sub>d</sub> vs. C<sub>trip</sub> CHARACTERISTICS on page 6/6.
5. The t<sub>d</sub> is a delay time due to signal transmission of each protection circuit.
6. If short-circuit current flows at turn-on, the controlled time detect short circuit (t<sub>d</sub>) is included to the t<sub>d</sub> of short-circuit protect delay time.  
The t<sub>d</sub> can be changed through C<sub>trip</sub>.  
As a gate shutdown of IGBT modules within 10 μs is recommended, C<sub>trip</sub> should be below 220pF in order to set the maximum of t<sub>d</sub> below 10μs

**CONTROL OF IGBT MODULE DRIVER**

The timing chart for control of IGBT module drivers with electrical isolation between the input and output is as follows.



Timing chart when protection circuit operates under over-current (short circuit) with power supply applied.

**DESCRIPTION OF TIMING CHART**

- (1) When  $V_{CC}$  is within 10 to 15 voltages, S/C detect output ( $V_{FO}$ ) is in the low state. The output voltage remains in the low state for 3 to 6 ms. If the power supply is applied in the high state of input signal, the output ( $V_o$ ) remains in the low state. But  $V_{FO}$  becomes in the low state for 3 to 6 ms. After normal function starts, if  $V_{CC}$  is below the start voltage of protection circuit (Typ. 15.2V),  $V_{FO}$  is low and  $V_o$  is low voltage for the same period.
- (2) After  $V_{FO}$  returns to high level, control signal should be applied.
- (3) If over-current or short-circuit current flows between the collector and emitter of IGBT modules, the internal RTC circuit pulls the gate voltage down below 11V
- (4) When the turn-on of IGBT coincides with over-current or short-circuit current, the timer circuit functions after  $t_c$ .
- (5) After  $t_d$  from the short-circuit or over-current, the output voltage of  $V_o$  is low and  $V_{FO}$  is low voltage at the same time. The output remains low during the operating time of timer circuit regardless of input signals.
- (6) If the input signal is low level after  $t_{timer}$ , the protection function is cancelled. And then  $V_{FO}$  returns to high voltage.

CHARACTERISTICS CURVES

